

BFN18

NPN Silicon High-Voltage Transistors

Data Sheet

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Revision History

| Page or Item | Subjects (major changes since previous revision) |
|---------------------------------|--|
| Revision 1.0, 2010-10-13 | |
| | Converted to the new IFX Template. |
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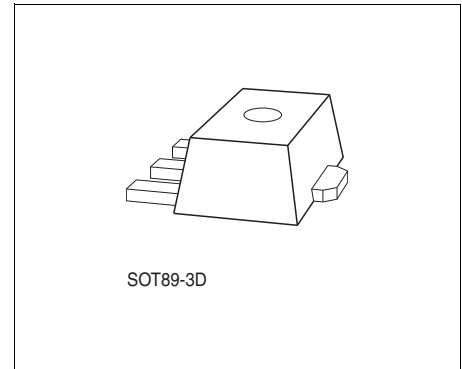
Table of Contents

| | | |
|----------|---|----|
| | Table of Contents | 4 |
| | List of Figures | 5 |
| | List of Tables | 6 |
| 1 | Features | 7 |
| 2 | Electrical Characteristics | 8 |
| 3 | Characteristic DC Diagrams | 10 |
| 4 | Package Information SOT89 | 12 |

1 Features

Main features:

- Suitable for video output stages TV sets and switching power supplies
- High breakdown voltage
- Low collector-emitter saturation voltage
- Complementary types: BFN19 (PNP)
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101



1) Pb-containing package may be available upon special request

| Product Name | Package | Pin Configuration | | | | Marking |
|--------------|---------|-------------------|-------|-------|-------|---------|
| | | 1 = B | 2 = C | 3 = E | 4 = C | |
| BFN18 | SOT89 | 1 = B | 2 = C | 3 = E | 4 = C | DE |

2 Electrical Characteristics

Table 1 Absolute Maximum Ratings

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|-----------|--------|------|------|------|-----------------------|
| | | Min. | Typ. | Max. | | |
| Collector-emitter voltage | V_{CEO} | – | – | 300 | V | – |
| Collector-base voltage | V_{CBO} | – | – | 300 | V | – |
| Emitter-base voltage | V_{EBO} | – | – | 5 | V | – |
| Collector current | I_C | – | – | 200 | mA | – |
| Peak collector current | I_{CM} | – | – | 500 | mA | – |
| Base current | I_B | – | – | 100 | mA | – |
| Peak base current | I_{BM} | – | – | 200 | mA | – |
| Total power dissipation- $T_S = 120\text{ °C}$ | P_{tot} | – | – | 1.5 | W | – |
| Junction temperature | T_j | – | – | 150 | °C | – |
| Storage temperature | T_{stg} | -65 | – | 150 | °C | – |

Attention: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the device.

Table 2 Thermal Resistance

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|------------|--------|------|------|------|-----------------------|
| | | Min. | Typ. | Max. | | |
| Junction - soldering point ¹⁾ | R_{thJS} | – | – | ≤ 20 | K/W | – |

1) For calculation of R_{thJA} please refer to Application Note Thermal Resistance.

Table 3 DC Characteristics at $T_A = 25\text{ °C}$, Unless Otherwise Specified

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|---------------|--------|------|------|---------------|--|
| | | Min. | Typ. | Max. | | |
| Collector emitter breakdown voltage | $V_{(BR)CEO}$ | 300 | – | – | V | $I_C = 1\text{ mA}, I_B = 0$ |
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | 300 | – | – | V | $I_C = 100\text{ }\mu\text{A}, I_E = 0$ |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | 5 | – | – | V | $I_E = 100\text{ }\mu\text{A}, I_C = 0$ |
| Collector-base cutoff current | I_{CBO} | – | – | 0.1 | μA | $V_{CB} = 250\text{ V}, I_E = 0$ |
| | | – | – | 20 | | |
| Emitter-base cutoff current | I_{EBO} | – | – | 100 | nA | $V_{EB} = 5\text{ V}, I_C = 0$ |
| DC current gain ¹⁾ | h_{FE} | 25 | – | – | | $I_C = 1\text{ mA}, V_{CE} = 10\text{ V}$ |
| | | 40 | – | – | | $I_C = 10\text{ mA}, V_{CE} = 10\text{ V}$ |
| | | 30 | – | – | | $I_C = 30\text{ mA}, V_{CE} = 10\text{ V}$ |
| Collector-emitter saturation voltage ¹⁾ | V_{CEsat} | – | – | 0.5 | V | $I_C = 20\text{ mA}, I_B = 2\text{ mA}$ |
| Base emitter saturation voltage ¹⁾ | V_{BEsat} | – | – | 0.9 | V | $I_C = 20\text{ mA}, I_B = 2\text{ mA}$ |

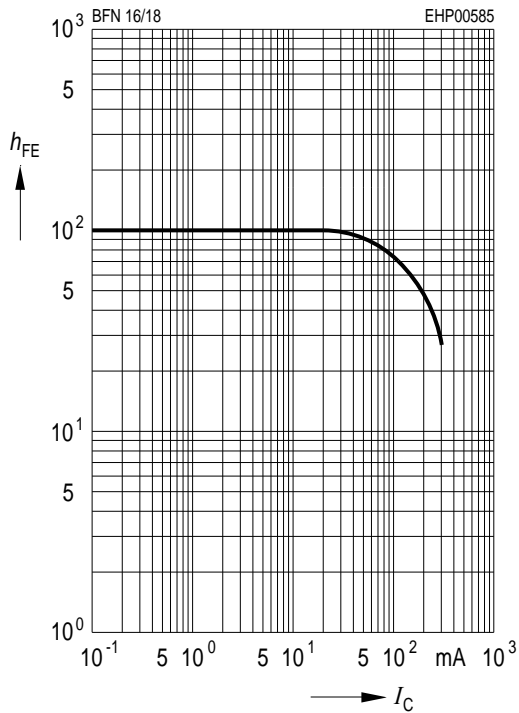
1)Pulse test: $t < 300\text{ }\mu\text{s}$; $D < 2\%$

Table 4 AC Characteristics at $T_A = 25\text{ °C}$

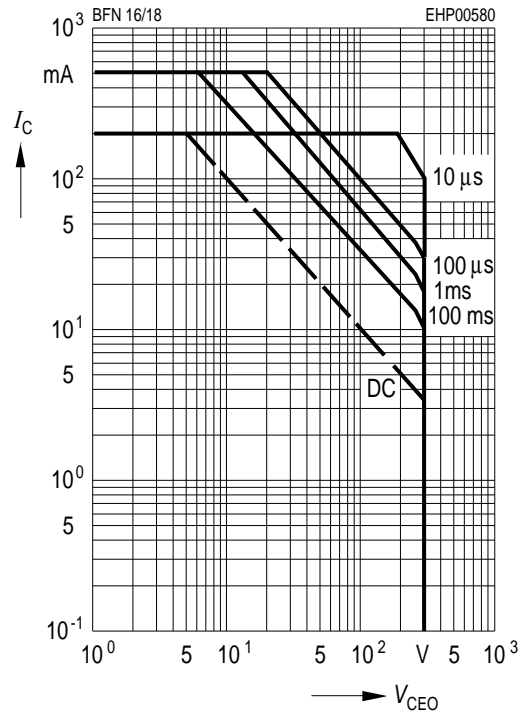
| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|----------------------------|----------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Transition frequency | f_T | – | 70 | – | MHz | $I_C = 20\text{ MHz}, V_{CE} = 10\text{ V}, f = 20\text{ MHz}$ |
| Collector base capacitance | C_{Cb} | – | 1.5 | – | pF | $V_{CB} = 30\text{ V}, f = 1\text{ MHz}$ |

3 Characteristic DC Diagrams

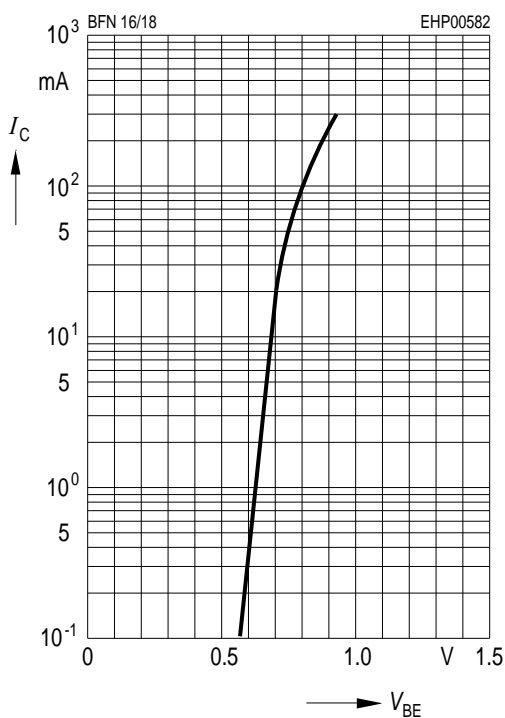
DC Current Gain
 $h_{FE} = f(I_C), V_{CE} = 10\text{ V}$



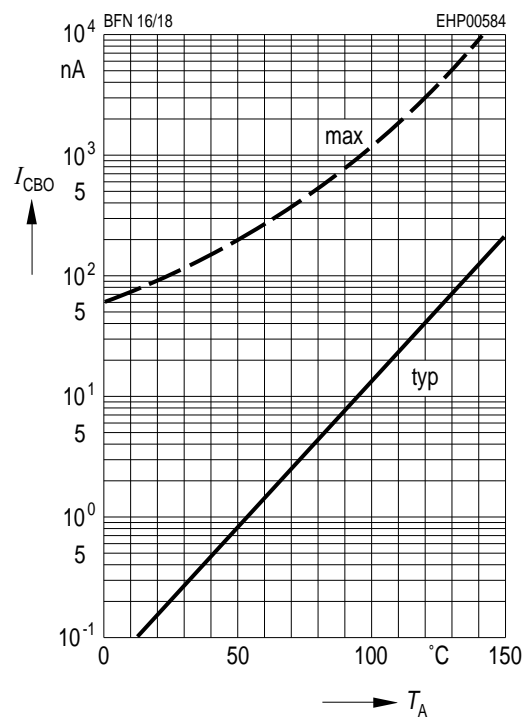
Operating Range
 $I_C = f(V_{CEO}), T_A = 25^\circ\text{C}, D = 0$



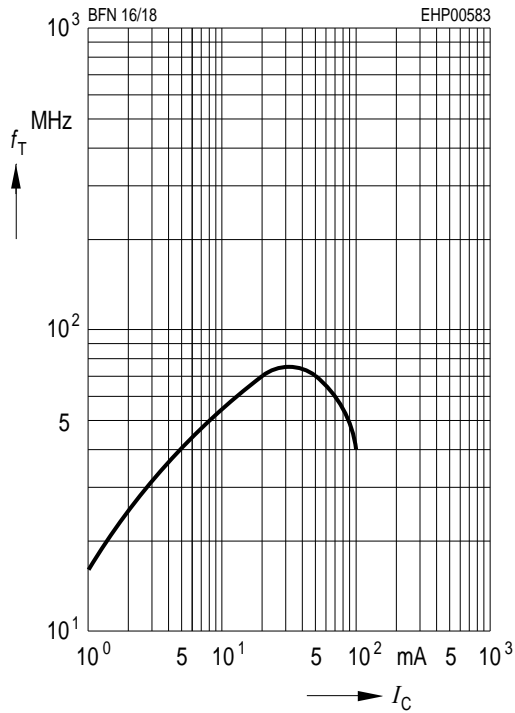
Collector Current
 $I_C = f(V_{BE}), V_{CE} = 10\text{ V}$



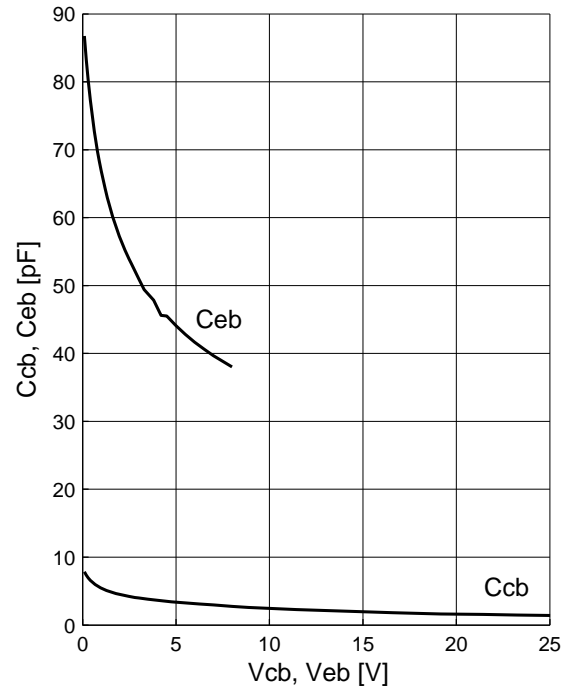
Collector Cutoff Current
 $I_{CBO} = f(T_A), V_{CBO} = 200\text{ V}$



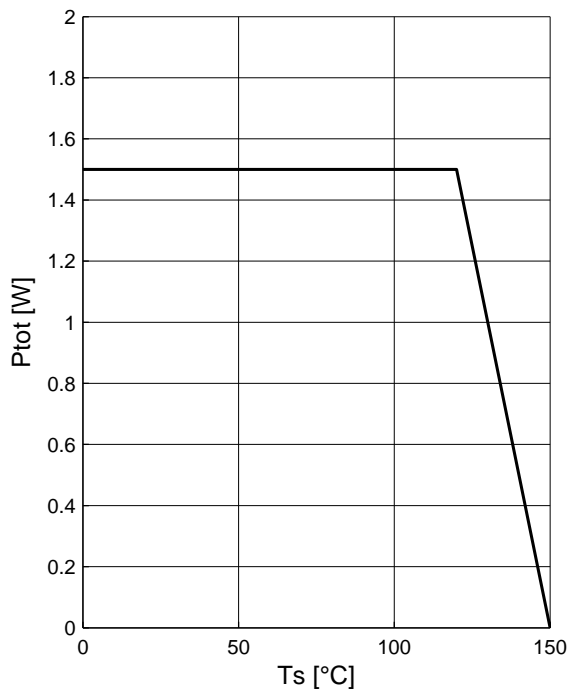
Transition Frequency
 $f_T = f(I_C), V_{CE} = 10\text{ V}$



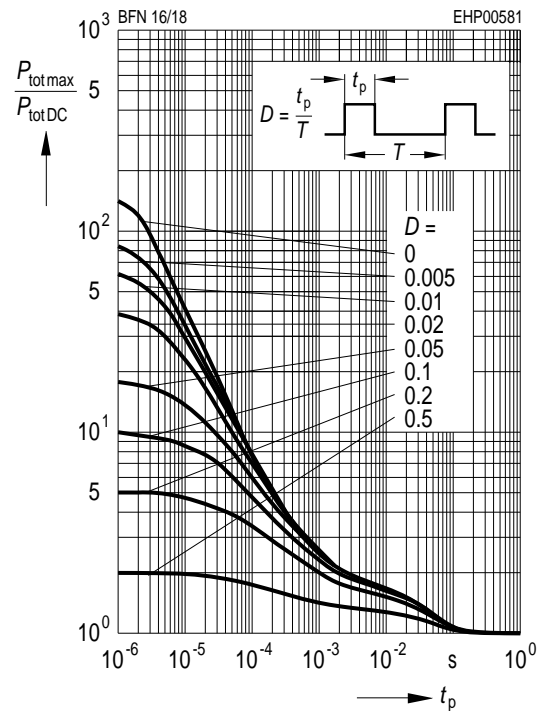
Collector Base Capacitance $C_{cb} = f(V_{CB})$
Emitter Base Capacitance $C_{eb} = f(V_{EB})$



Total Power Dissipation
 $P_{tot} = f(T_S)$



Permissible Pulse Load
 $P_{totmax} / P_{totDC} = f(T_S)$



4 Package Information SOT89

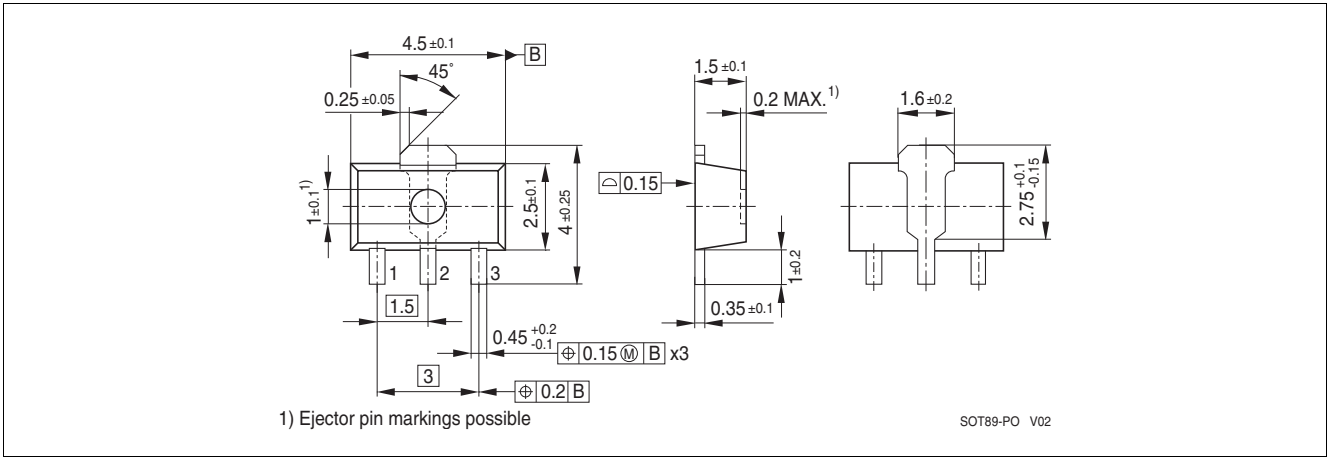


Figure 1 Package Outline

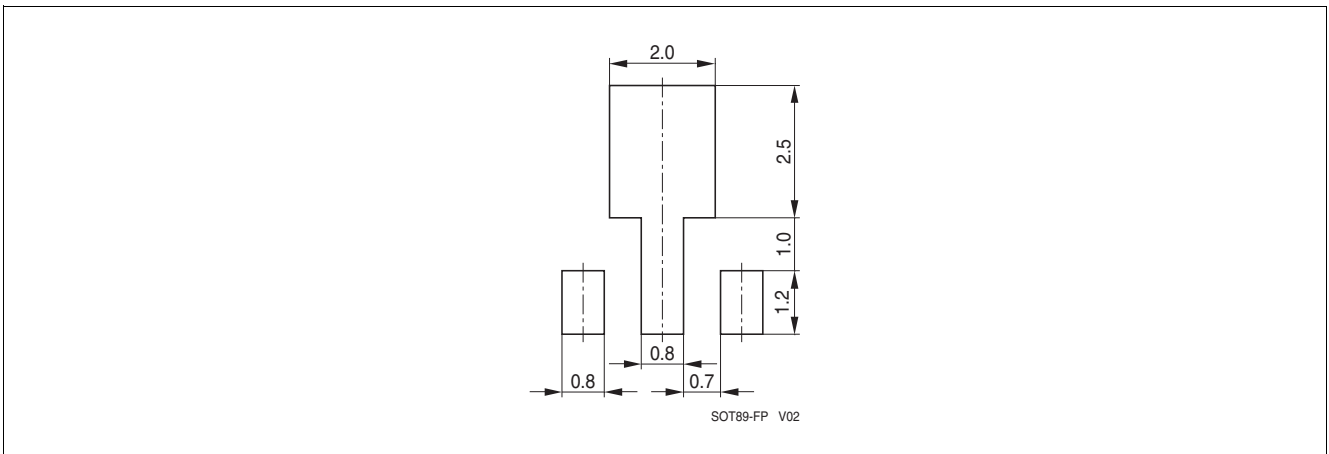


Figure 2 Package Foot Print

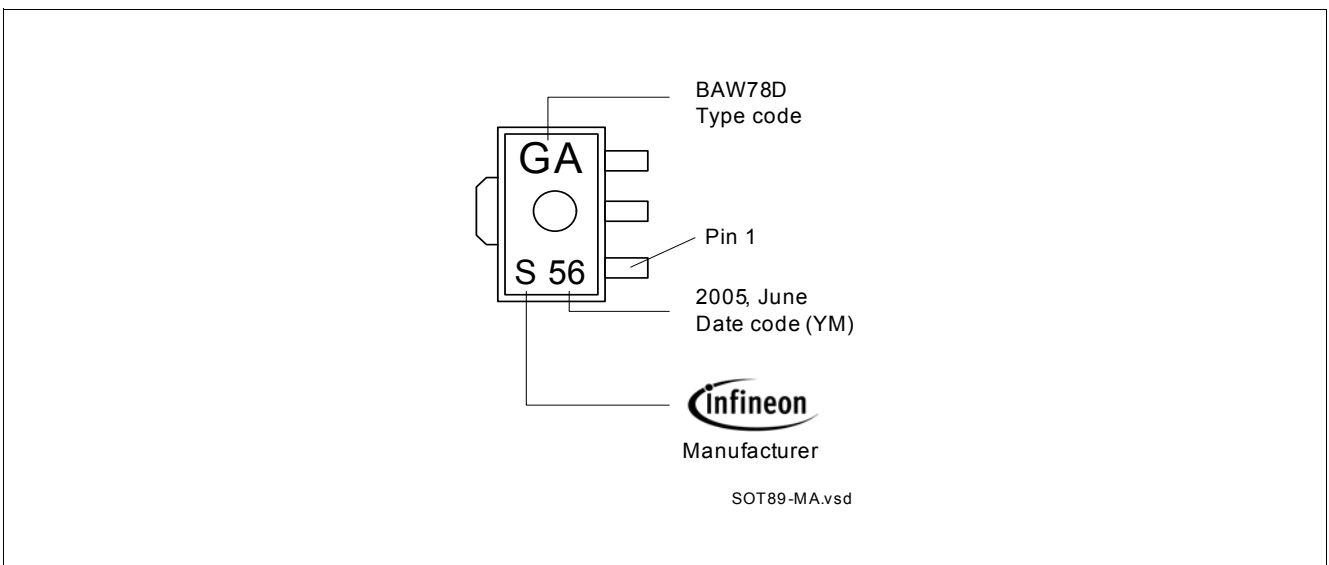


Figure 3 Marking Example

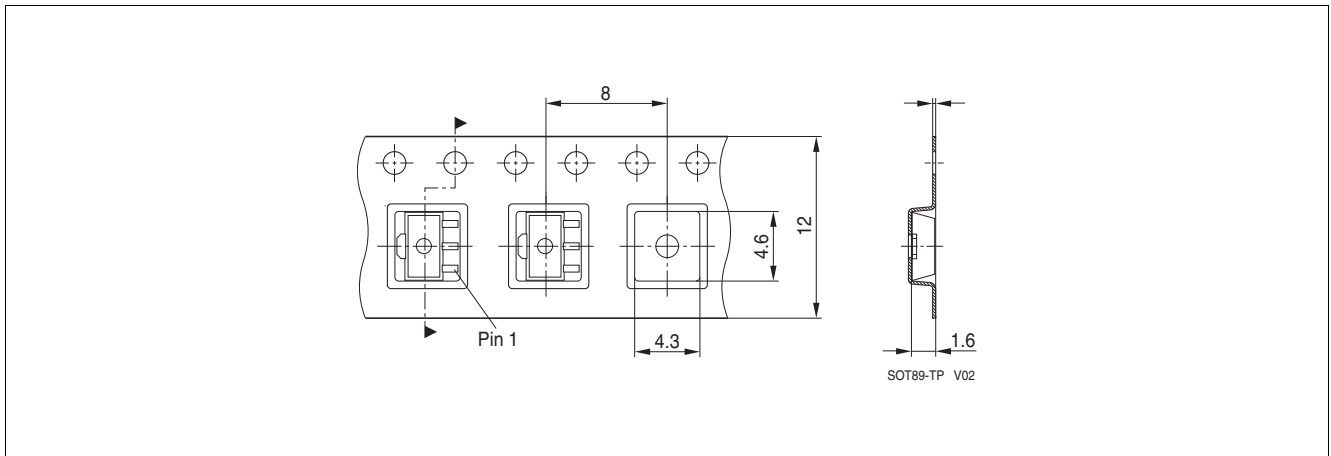


Figure 4 Tape Dimensions

Packing Description

Reel Ø180 mm = 1.000 Pieces/Reel

Reel Ø330 mm = 4.000 Pieces/Reel

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